

U.S.S.N. 10/077,720

Specification Amendments

Please replace the paragraph beginning on page 14, paragraph 0028 with the following rewritten paragraph:

0027 Figures 1A through 1C show a series of steps performed to complete an etching process in a semiconductor structure, for example, a via or contact hole. In Figures 1A through 1C is depicted a photoresist layer 12 overlying a DARC layer 10, followed by a low-k material 14 and finally an etching stop layer 16. In Figures 1A through 1C is represented the etching of, for example, a via hole 20 where the low-k material 14 is for example, an inter-metal dielectric (IMD). As shown in Figure 1A, an etching process with a chemistry that is capable of selectively etching an inorganic dielectric anti-reflective coating (DARC) layer is required in the first step. The DARC is preferably a nitride containing material and more preferably, at least one of silicon nitride, silicon oxynitride, and titanium nitride. The DARC may also be a low-k carbon containing dielectric material layer.

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Please replace the paragraph beginning on page 14, paragraph 0036 with the following rewritten paragraph:

0036 As a representative process for etching a low-k layer, it has been found that suitable pressures for the etching process are from about 40 to about 60 millitorr. Suitable levels of microwave power supplied to the plasma are from 1000 to about 1800 Watts. Hydrofluorocarbons Fluorocarbons such as C₄F₈, C₂F₆, or C₄F₆, or a mixture thereof is provided at an increased carbon to fluorine ratio of at least about ½ (i.e. a decreased suitable fluorine to carbon ratio of at least about 2) is preferably supplied with a flow rate from about 5 to about 15 sccm. Further, a nitrogen flow rate is preferably supplied from about 150 to about 300 sccm with an oxygen flow rate from about 2 to about 10 sccm.